

PNP EPITAXIAL SILICON TRANSISTOR (Version C1.0)

S8550

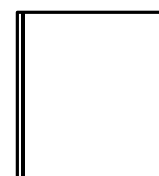
High Current Application

- ◇ High Collector current $I_c = -700\text{ mA}$
- ◇ High Collector Power Dissipation $P_c = 1\text{ W}$
- ◇ Complementary to S8050

ABSOLUTE MAXIMUM RATINGS

($T_a = 25^\circ\text{C}$)

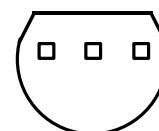
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base voltage	V_{EBO}	-6	V
Collector Current	I_C	-700	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$



TO-92

1 2 3

1. Emitter
2. Base
3. Collector



ELECTRICAL CHARACTERISTICS

($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -100\text{ }\mu\text{A}$	-40			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -10\text{ mA}$	-25			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -100\text{ }\mu\text{A}$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{ V}$			-100	nA
DC current gain	h_{FE}					
		$I_C = -100\text{ mA}$ $V_{CE} = -1\text{ V}$	85		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{ mA}$ $I_B = -80\text{ mA}$		-0.28	-0.5	V

* h_{FE} Classification: B:85~160 , C:120~200 , D:160~300